

Silicon NPN Power Transistors

DESCRIPTION

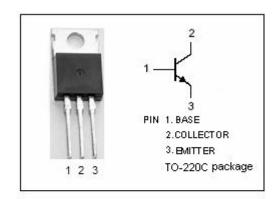
- DC Current Gain -hFE = 30(Min)@ IC= -0.3A
- · Collector-Emitter Sustaining Voltage-
 - : $V_{CEO(SUS)}$ = 40V(Min)- TIP41; 60V(Min)- TIP41A 80V(Min)- TIP41B; 100V(Min)- TIP41C
- Complement to Type TIP42/42A/42B/42C

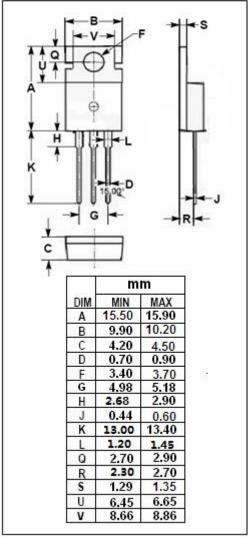
APPLICATIONS

 Designed for use in general purpose amplifer and switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

ADSOLUTE MAXIMUM RATINGS(Ta=25 C)									
SYMBOL	PARAMETER	VALUE	UNIT						
V _{СВО}	Collector-Base Voltage	TIP41	40						
		TIP41A	60						
		TIP41B	80	V					
		TIP41C	100						
V _{CEO}	Collector-Emitter Voltage	TIP41	40	V					
		TIP41A	60						
		TIP41B	80						
		TIP41C	100						
V _{EBO}	Emitter-Base Voltage	5	V						
Ic	Collector Current-Continuous		6	Α					
Ісм	Collector Current-Peak	10	Α						
Ι _Β	Base Current	2	Α						
Pc	Collector Power Dissipation T _c =25℃		65	· W					
	Collector Power Dissipation T _a =25°C		2						
Tj	Junction Temperature	150	$^{\circ}$						
T _{stg}	Storage Temperature Rang	-65~150	$^{\circ}\!$						





Ordering Information

Product	Package	Packaging
TIP41CT1TL	TO-220C	Tube

V01



ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	MAX	UNIT
Vceo(sus) *	Collector-Emitter Sustaining Voltage	TIP41	Ic= 30mA; I _B = 0	40		V
		TIP41A		60		
		TIP41B		80		
		TIP41C		100		
V _{CE(sat)} *	Collector-Emitter Saturation Voltage		I _C = 6A ;I _B = 0.6A		1.5	V
V _{BE(on)} *	Base-Emitter On Voltage		I _C = 6A; V _{CE} = 4V		2.0	V
I _{CES}	Collector Cutoff Current	TIP41	V _{CE} = 40V; V _{EB} = 0		0.4	mA
		TIP41A	V _{CE} = 60V; V _{EB} = 0			
		TIP41B	V _{CE} = 80V; V _{EB} = 0		0.4	
		TIP41C	V _{CE} =100V; V _{EB} = 0			
I _{CEO}	Collector Cutoff Current	TIP41/41A	V _{CE} =30V; I _B = 0		0.7	mA
		TIP41B/41C	V _{CE} = 60V; I _B = 0			
I _{EBO}	Emitter Cutoff Current		V _{EB} = 5V; I _C = 0		1.0	mA
h _{FE-1} *	DC Current Gain		I _C =0.3A; V _{CE} =4V	30		
h _{FE-2} *	DC Current Gain		I _C = 3A; V _{CE} = 4V	15	75	
f _T	Current-Gain—Bandwidth Product		I _C = 0.5A ;V _{CE} = 10V	3		MHz

^{*} Pulse Test: PW≤300µs, Duty Cycle≤2%

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